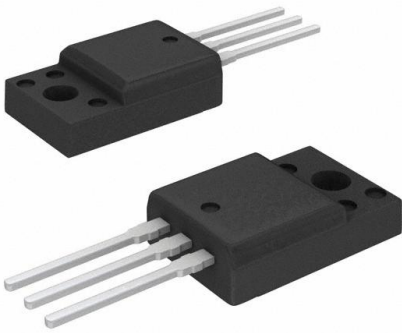


FCPF20N60T Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FCPF20N60T-DG
Manufacturer	onsemi
Manufacturer Product Number	FCPF20N60T
Description	MOSFET N-CH 600V 20A TO220F
Detailed Description	N-Channel 600 V 20A (Tc) 39W (Tc) Through Hole T O-220F-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

FCPF20N60T

Series:

SuperFET™

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

600 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

5V @ 250µA

Vgs (Max):

±30V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-220F-3

Base Product Number:

FCPF20

Manufacturer:

onsemi

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

20A (Tc)

Rds On (Max) @ Id, Vgs:

190mOhm @ 10A, 10V

Gate Charge (Qg) (Max) @ Vgs:

98 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

3080 pF @ 25 V

Power Dissipation (Max):

39W (Tc)

Mounting Type:

Through Hole

Package / Case:

TO-220-3 Full Pack

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

Not Applicable

ECCN:

EAR99

MOSFET – N-Channel, SuperFET®

600 V, 20 A, 190 mΩ

FCP20N60, FCPF20N60

Description

SuperFET MOSFET is onsemi's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.

Features

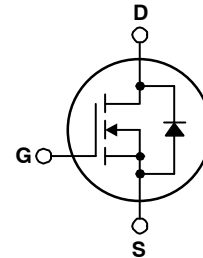
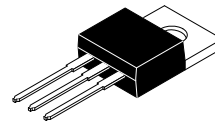
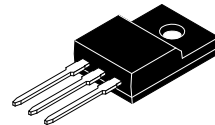
- 650 V @ $T_j = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 150\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 75\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 165\text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Solar Inverter
- AC – DC Power Supply

V_{DS}	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	190 mΩ @ 10 V	20 A*

*Drain current limited by maximum junction temperature.


N-CHANNEL MOSFET

**TO-220-3LD
CASE 340AT**

**TO-220 Fullpack, 3-Lead
/ TO-220F-3SG
CASE 221AT**

MARKING DIAGRAM



XXX20N60 = Device Code (XXX = FCP, FCPF)
 A = Assembly Location
 YWW = Date Code (Year & Week)
 ZZ = Assembly Lot

ORDERING INFORMATION

Device	Package	Shipping
FCP20N60	TO-220	1000 Units / Tube
FCPF20N60	TO-220F	1000 Units / Tube

FCP20N60, FCPF20N60**MOSFET MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	FCP20N60	FCPF20N60	Unit
V_{DSS}	Drain-Source Voltage	600		V
I_D	Drain Current	- Continuous, $T_C = 25^\circ\text{C}$	20	20*
		- Continuous, $T_C = 100^\circ\text{C}$	12.5	12.5*
		- Pulsed (Note 1)	60	60*
I_{DM}				
V_{GSS}	Drain-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	690		mJ
I_{AR}	Avalanche Current (Note 1)	20		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	20.8		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	208	39
		-Derate above $= 25^\circ\text{C}$	1.67	0.3
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Drain current limited by maximum junction temperature.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{AS} = 10\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 20\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	FCP20N60	FCPF20N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.6	3.2	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	

FCP20N60, FCPF20N60**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_J = 25^\circ\text{C}$	600	–	–	V
		$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_J = 150^\circ\text{C}$	–	650	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C	–	0.6	–	$\text{V}/^\circ\text{C}$
BV_{DS}	Drain–Source Avalanche Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 20 \text{ A}$	–	700	–	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	–	–	1	μA
		$V_{DS} = 480 \text{ V}, T_C = 125^\circ\text{C}$	–	–	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	–	–	± 100	μA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	3.0	–	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	–	0.15	0.19	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_D = 10 \text{ A}$	–	17	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	–	2370	3080	pF
C_{oss}	Output Capacitance		–	1280	1665	pF
C_{riss}	Reverse Transfer Capacitance		–	95	–	pF
C_{oss}	Output Capacitance	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	–	65	85	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0 \text{ V}, V_{GS} = 400 \text{ V}, V_{GS} = 0 \text{ V}$	–	165	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	$V_{DS} = 480 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4)	–	75	98	nC
Q_{gs}	Gate to Source Gate Charge		–	13.5	18	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	36	–	nC
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 300 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}, R_G = 25 \Omega$ (Note 4)	–	62	135	ns
t_r	Turn–On Rise Time		–	140	290	ns
$t_{d(off)}$	Turn–Off Delay Time		–	230	470	ns
t_f	Turn–Off Fall Time		–	65	140	ns
DRAIN–SOURCE DIODE CHARACTERISTICS						
I_S	Maximum Continuous Drain to Source Diode Forward Current		–	–	20	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		–	–	60	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 20 \text{ A}$	–	–	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 20 \text{ A},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	–	530	–	ns
Q_{rr}	Reverse Recovery Charge		–	10.5	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

FCP20N60, FCPF20N60

TYPICAL PERFORMANCE CHARACTERISTICS

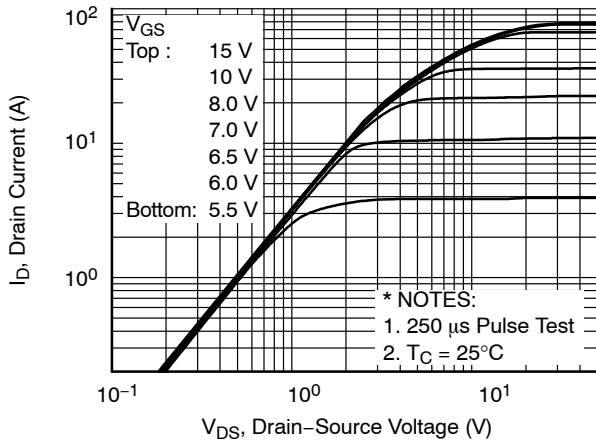


Figure 1. On-Region Characteristics

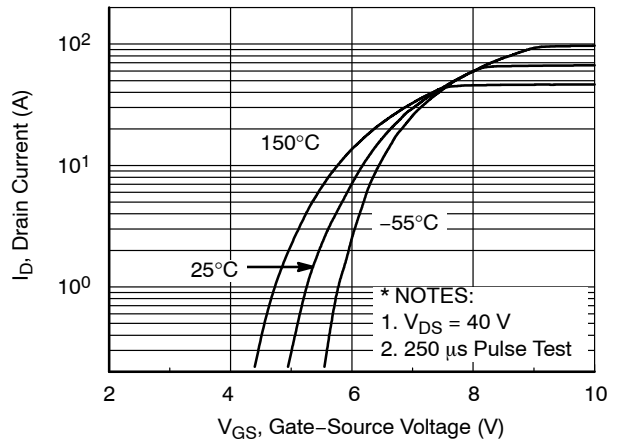


Figure 2. Transfer Characteristics

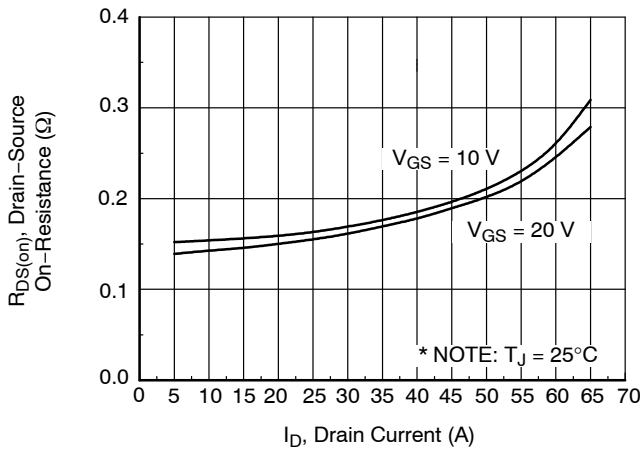


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

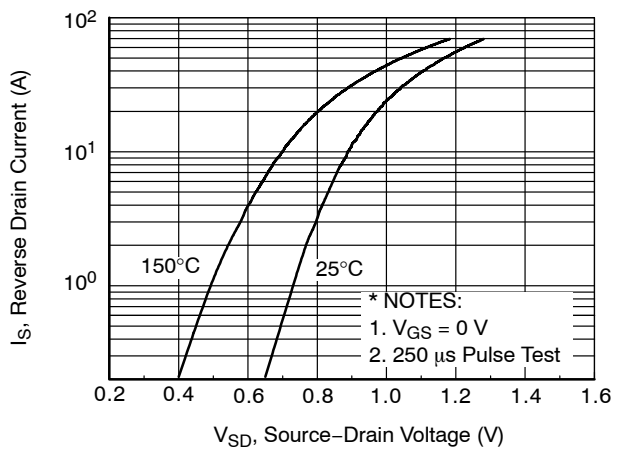


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

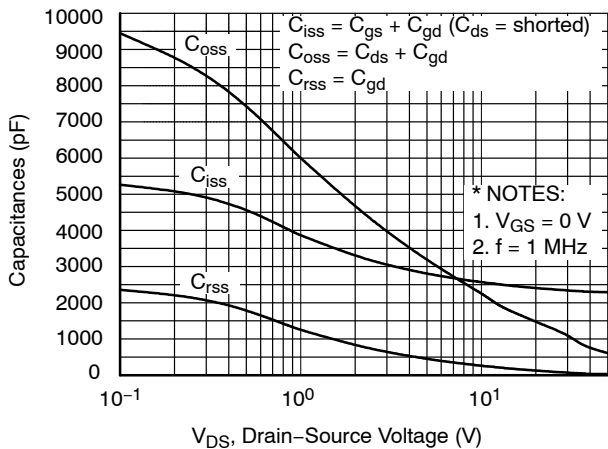


Figure 5. Capacitance Characteristics

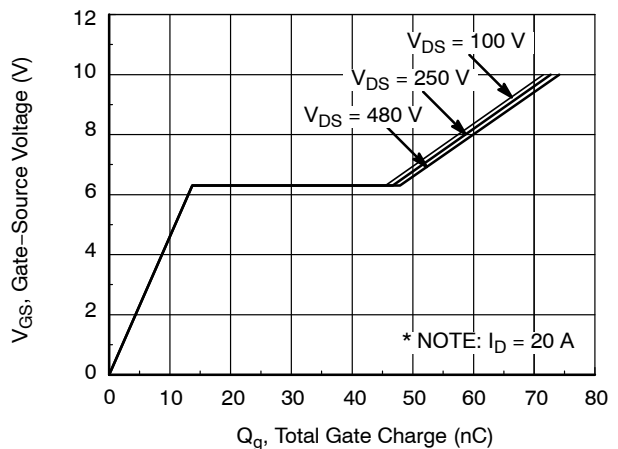


Figure 6. Gate Charge Characteristics

FCP20N60, FCPF20N60

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

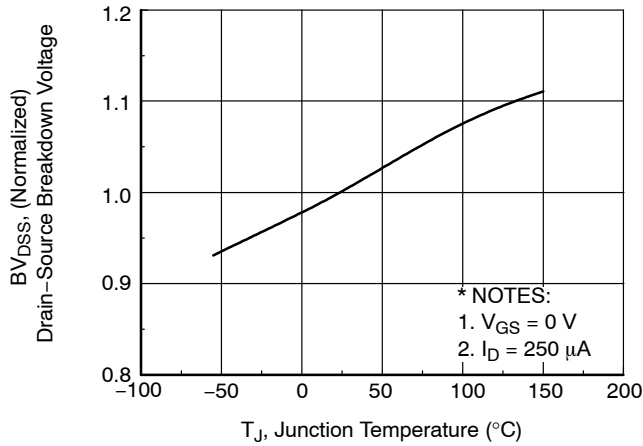


Figure 7. Breakdown Voltage Variation vs. Temperature

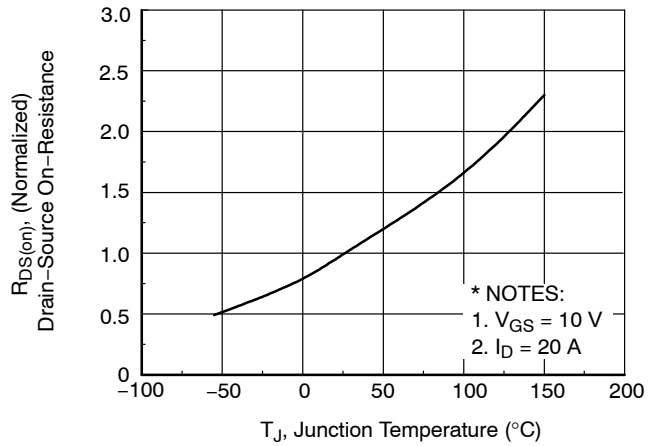


Figure 8. On-Resistance Variation vs. Temperature

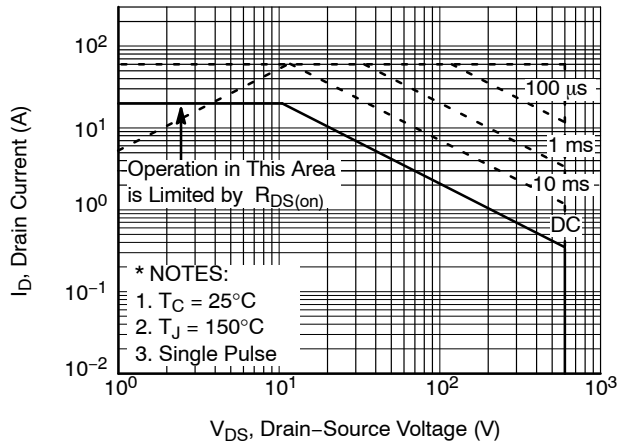


Figure 9. Maximum Safe Operating Area for FCP20N60

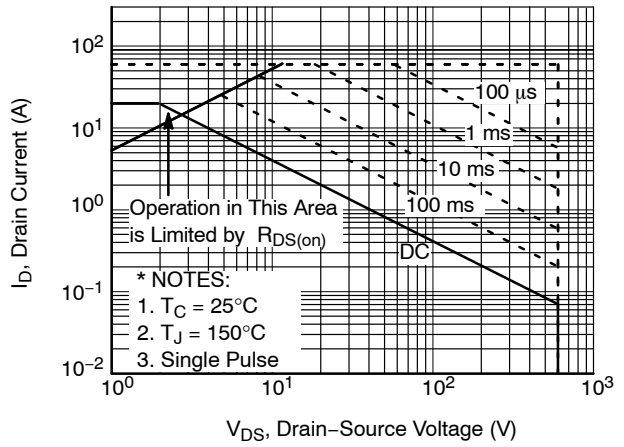


Figure 10. Maximum Safe Operating Area for FCPF20N60

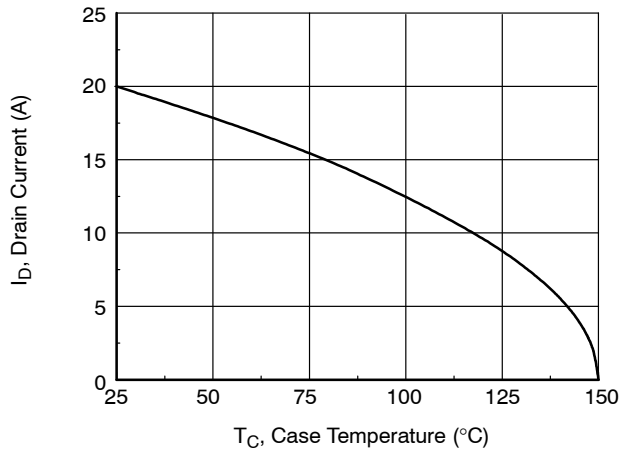


Figure 11. Maximum Drain Current vs. Case Temperature

FCP20N60, FCPF20N60

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

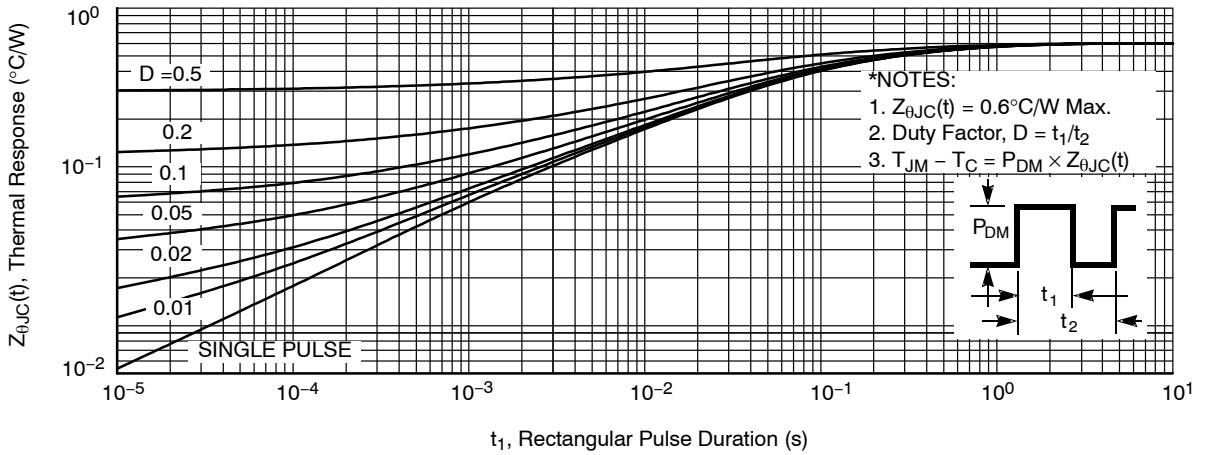


Figure 12. Transient Thermal Response Curve for FCP20N60

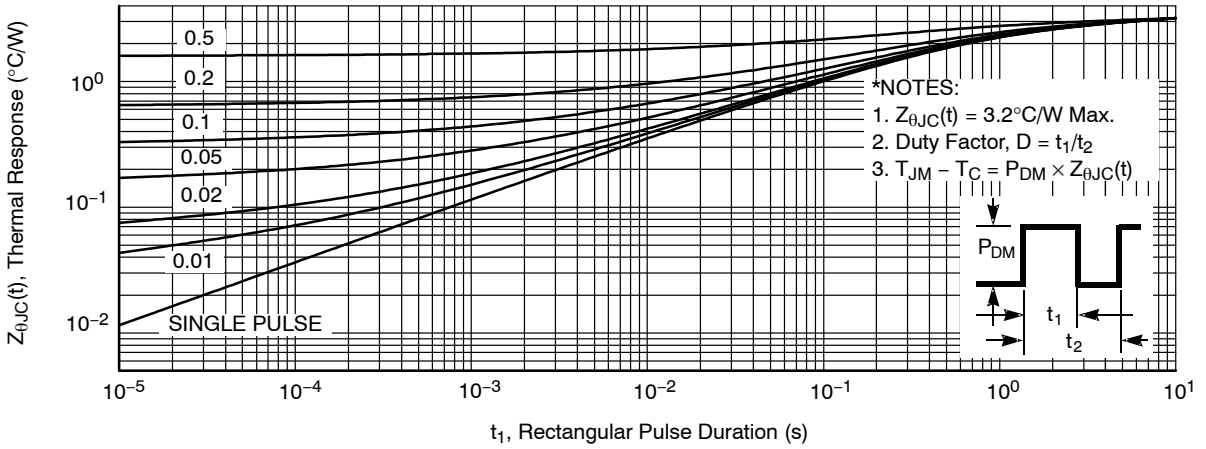


Figure 13. Transient Thermal Response Curve for FCPF20N60

FCP20N60, FCPF20N60

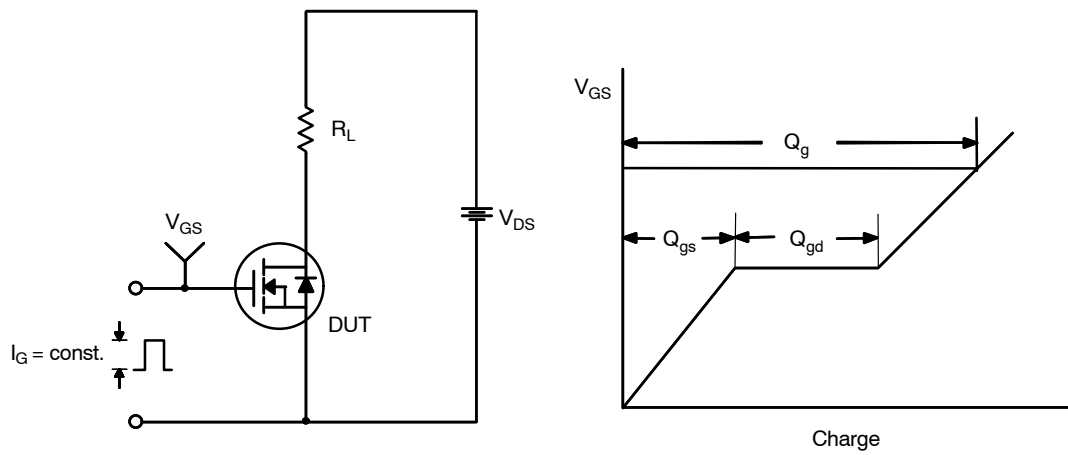


Figure 14. Gate Charge Test Circuit & Waveform

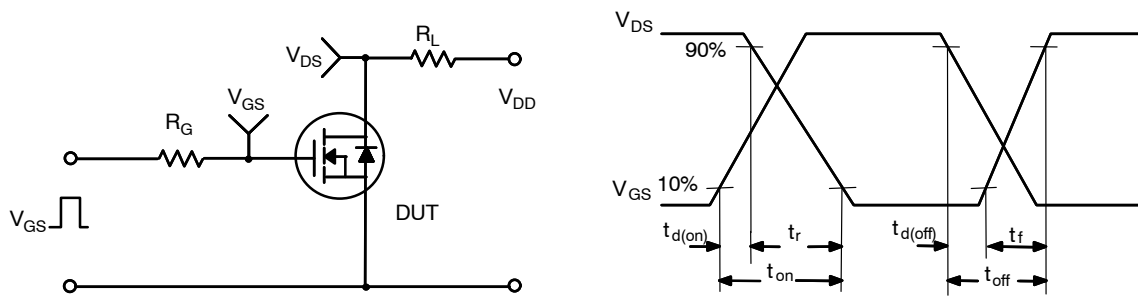


Figure 15. Resistive Switching Test Circuit & Waveforms

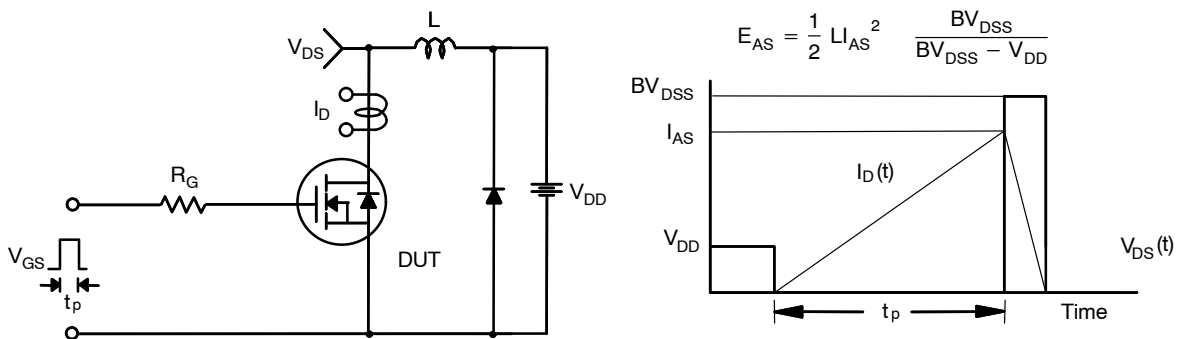


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

FCP20N60, FCPF20N60

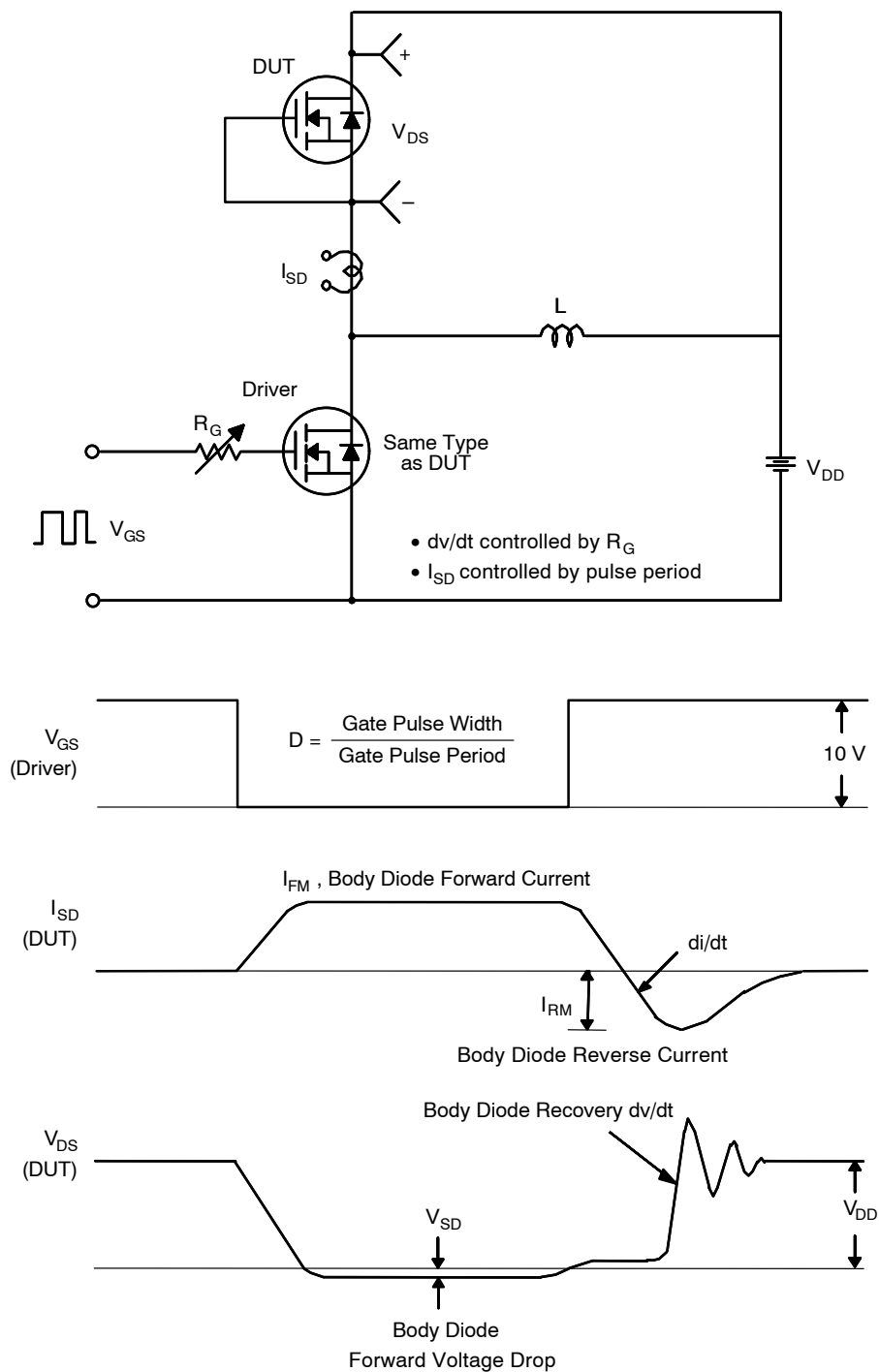


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

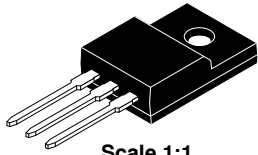
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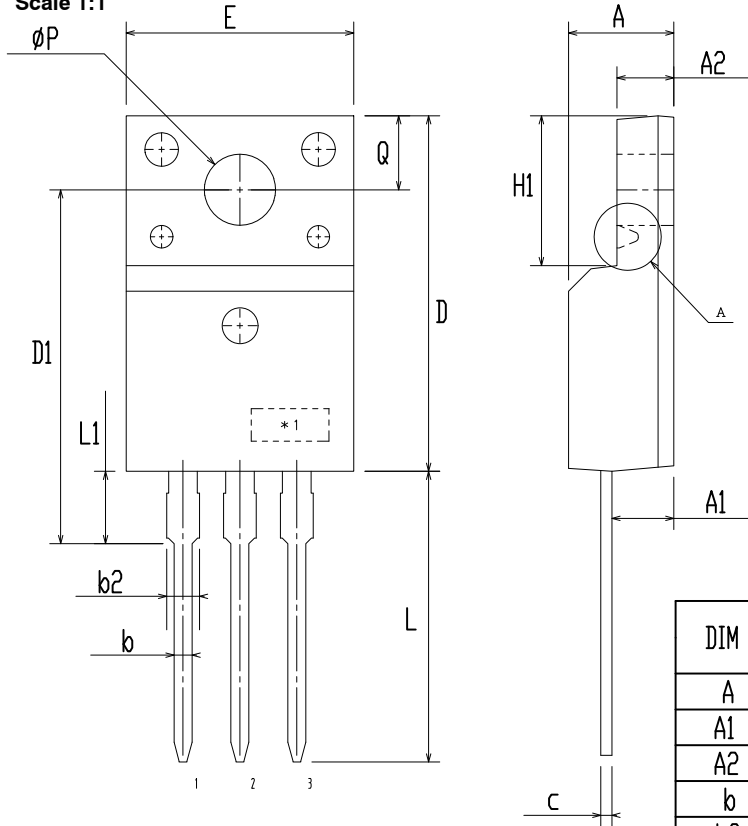
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TO-220 Fullpack, 3-Lead / TO-220F-3SG
CASE 221AT
ISSUE B

DATE 19 JAN 2021



Scale 1:1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
∅ P	2.98	3.18	3.38
∅ P1	~	1.00	~
Q	3.20	3.30	3.40

NOTES:

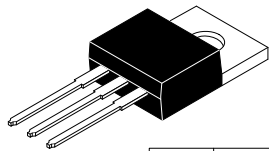
- A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.
- C. OPTION 1 - WITH SUPPORT PIN HOLE
OPTION 2 - NO SUPPORT PIN HOLE

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DESCRIPTION:	TO-220 FULLPACK, 3-LEAD / TO-220F-3SG	PAGE 1 OF 1

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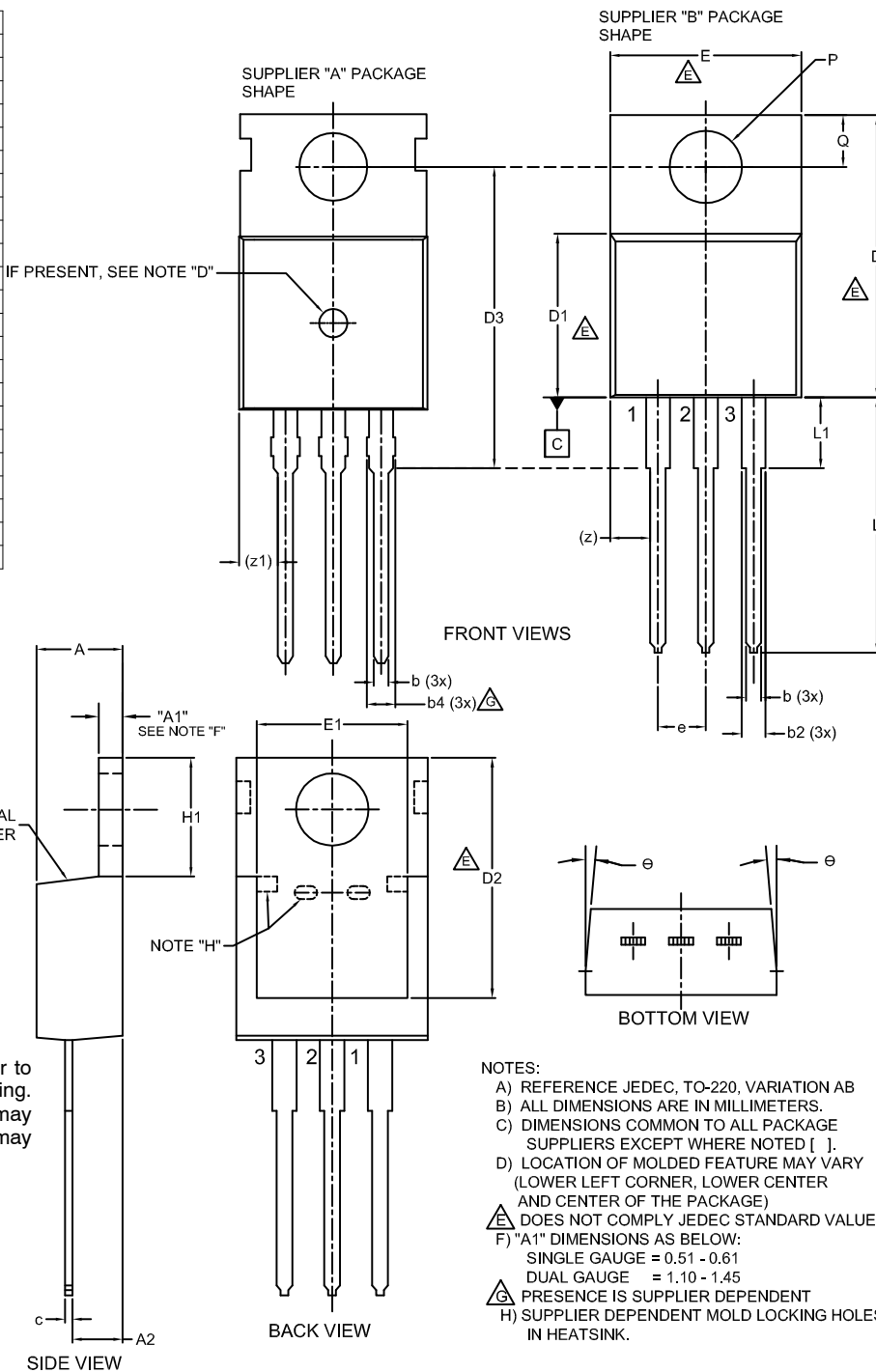
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



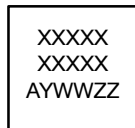
**TO-220-3LD
CASE 340AT
ISSUE B**

DATE 08 AUG 2022

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.00	--	4.70
A1	SEE NOTE "F"		
A2	2.10	--	2.85
b	0.55	--	1.00
b2	1.10	--	1.62
b4	1.42	--	1.62
c	0.36	--	0.60
D	13.90	--	16.30
D1	8.13	--	9.40
D2	11.50	--	14.30
D3	15.42	--	16.51
E	9.65	--	10.67
E1	7.59	--	8.65
e	2.40	--	2.67
H1	6.06	--	6.69
L	12.70	--	14.04
L1	2.70	--	4.10
P	3.50	--	4.00
Q	2.50	--	3.40
z	2.13 REF		
z1	2.06 REF		
θ	3°	--	5°



GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

- NOTES:
- A) REFERENCE JEDEC, TO-220, VARIATION AB
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
 - D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
 - ⚠ DOES NOT COMPLY JEDEC STANDARD VALUE.
 - F) "A1" DIMENSIONS AS BELOW:
 SINGLE GAUGE = 0.51 - 0.61
 DUAL GAUGE = 1.10 - 1.45
 - ⚠ PRESENCE IS SUPPLIER DEPENDENT
 - H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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DESCRIPTION:	TO-220-3LD	PAGE 1 OF 1

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